

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

Please rewrite claim 1 as follows.

**Listing of Claims:**

1. (currently amended) A substrate usable for an acoustic surface wave device, comprising:  
a base material made of C-faced sapphire single crystal; and  
an AlN film having crystallinity of 90 arcsec or below in full width at half maximum (FWHM) of X-ray rocking curve and a surface flatness of 20Å or below which is formed by a metal organic chemical vapor deposition (MOCVD) method using ~~trimethylaluminum~~ trimethylaluminum and ammonia as raw material gases.

2. (original) A substrate as defined in claim 1, further comprising a surface nitride layer at the main surface of the base material on which the AlN film is formed.

Claims 3-5: (cancelled)

6. (previously presented) An acoustic surface wave device, comprising:  
a substrate composed of a base material made of C-faced sapphire single crystal and an AlN film, formed on the base material, having crystallinity of 90 arcsec or below in full width at half maximum (FWHM) of X-ray rocking curve and a surface flatness of 20Å or below; and  
inter digital type electrodes.

7. (original) An acoustic surface wave device as defined in claim 6, wherein the substrate includes a surface nitride layer at the main surface of the base material on which the AlN film is formed.